

isc Silicon PNP Power Transistor

2SA808

DESCRIPTION

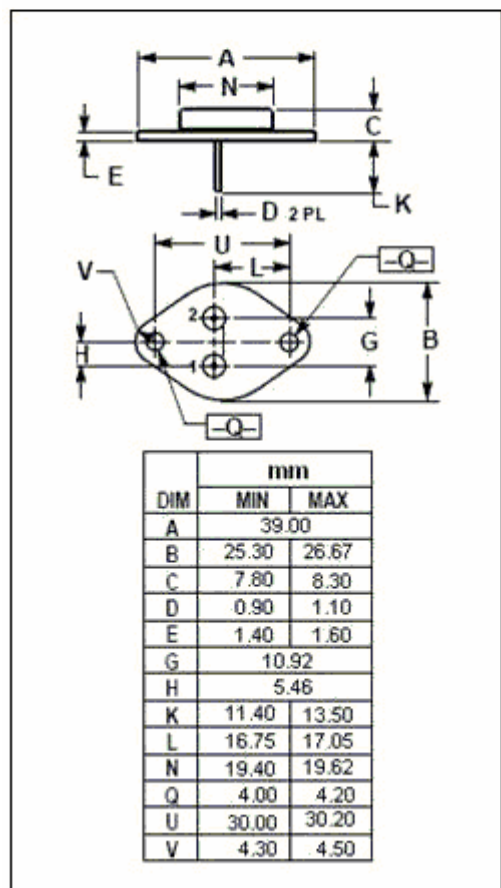
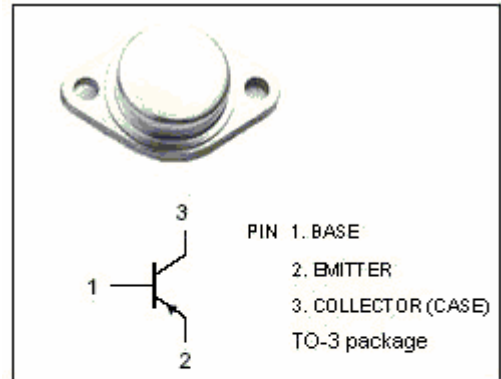
- High Power Dissipation-  
:  $P_C = 50W(\text{Max.}) @ T_C = 25^\circ\text{C}$
- Collector-Emitter Breakdown Voltage-  
:  $V_{(BR)CEO} = -80V(\text{Min.})$

APPLICATIONS

- Designed for general purpose applications.

ABSOLUTE MAXIMUM RATINGS( $T_a = 25^\circ\text{C}$ )

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	-80	V
$V_{CEO}$	Collector-Emitter Voltage	-80	V
$V_{EBO}$	Emitter-Base Voltage	-6	V
$I_C$	Collector Current-Continuous	-6	A
$I_B$	Base Current-Continuous	-3	A
$P_C$	Collector Power Dissipation @ $T_C = 25^\circ\text{C}$	50	W
$T_j$	Junction Temperature	150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature	-65~150	$^\circ\text{C}$



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## ELECTRICAL CHARACTERISTICS

T<sub>j</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = -50mA ; I <sub>B</sub> = 0	-80			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = -3A; I <sub>B</sub> = -0.3A			-1.5	V
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = -80V; I <sub>E</sub> = 0			-1.0	mA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = -6V; I <sub>C</sub> = 0			-1.0	mA
h <sub>FE</sub>	DC Current Gain	I <sub>C</sub> = -3A; V <sub>CE</sub> = -4V	20			
f <sub>T</sub>	Current-Gain—Bandwidth Product	I <sub>E</sub> = 0.5A; V <sub>CE</sub> = -12V		10		MHz

## Switching times

t <sub>r</sub>	Rise Time	I <sub>C</sub> = -3A , R <sub>L</sub> = 3 Ω , V <sub>CC</sub> = -10V I <sub>B1</sub> = -0.3A; I <sub>B2</sub> = 50mA		1.2		μ s
t <sub>stg</sub>	Storage Time			1.8		μ s
t <sub>f</sub>	Fall Time			0.3		μ s